MOSFETs Silicon N-Channel MOS (U-MOSVII)

TPCF8004

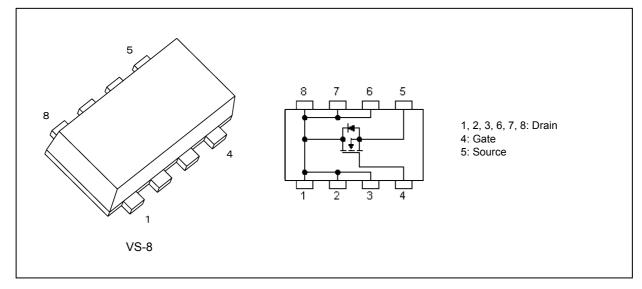
1. Applications

Lithium-Ion Secondary Batteries

2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 19 \text{ m}\Omega$ (typ.) (VGS = 10 V)
- (3) Low leakage current: I_{DSS} = 10 μ A (max) (V_{DS} = 30 V)
- (4) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_D = 0.1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)		(Note 1)	Ι _D	7	A
Drain current (pulsed)		(Note 1)	I _{DP}	28	
Power dissipation	(t = 5 s)	(Note 2)	PD	2.5	W
Power dissipation	(t = 5 s)	(Note 3)	PD	0.7	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	31	mJ
Avalanche current			I _{AR}	7	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2011-05 2014-02-17 Rev.2.0

5. Thermal Characteristics

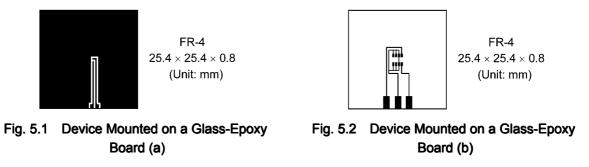
Characteristics				Max	Unit
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R _{th(ch-a)}	50	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)	R _{th(ch-a)}	178.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 1 Ω , I_{AR} = 7 A



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_		10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30	—	_	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.1 mA	1.3	_	2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 3.5 A	_	24	30	mΩ
		V _{GS} = 10 V, I _D = 3.5 A		19	24	

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		610	_	pF
Reverse transfer capacitance	C _{rss}		_	34	—	
Output capacitance	C _{oss}			130	—	
Switching time (rise time)	tr	See Figure 6.2.1.		3.0	_	ns
Switching time (turn-on time)	t _{on}			9.3	_	
Switching time (fall time)	t _f			4.5	_	
Switching time (turn-off time)	t _{off}			22	_	

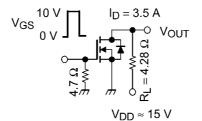


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

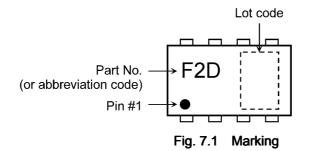
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 24$ V, V_{GS} = 10 V, I_D = 7 A	_	9.0	_	nC
Gate-source charge 1	Q _{gs1}		_	1.9	_	
Gate-drain charge	Q _{gd}		_	1.7	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

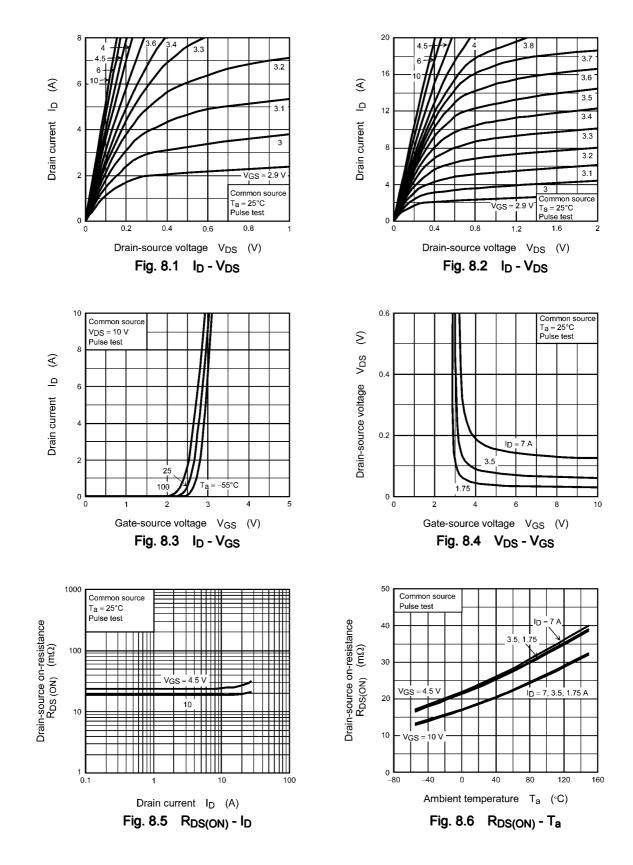
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note	5) I _{DRP}	—	_	—	28	А
Diode forward voltage	V _{DSF}	I _{DR} = 7 A, V _{GS} = 0 V			-1.2	V

Note 5: Ensure that the channel temperature does not exceed 150°C.

7. Marking



8. Characteristics Curves (Note)



0.

0**L**

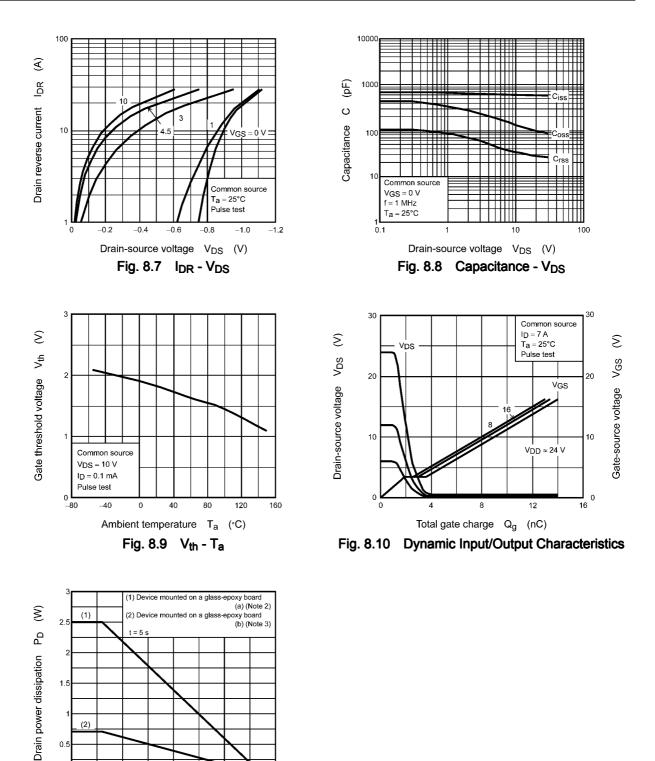
40

80

Ambient temperature T_a (°C) Fig. 8.11 PD - Ta (Guaranteed Maximum)

120

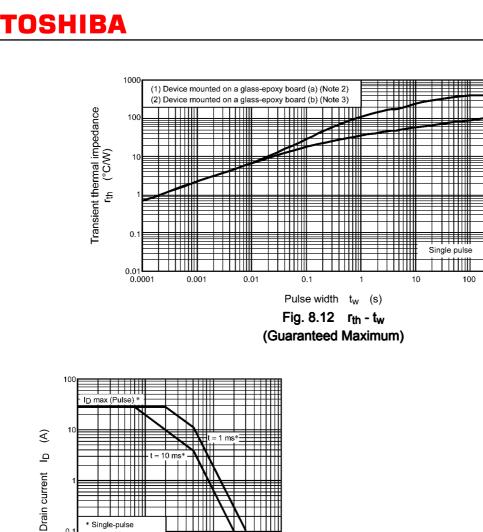
160



6

(2)

1000



ф

Drain-source voltage V_{DS} (V) Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

VDSS

10

100

* Single-pulse

linearly with increase in temperature

1

Ta = 25°C Curves must be derated

0.1

0.01 0.1

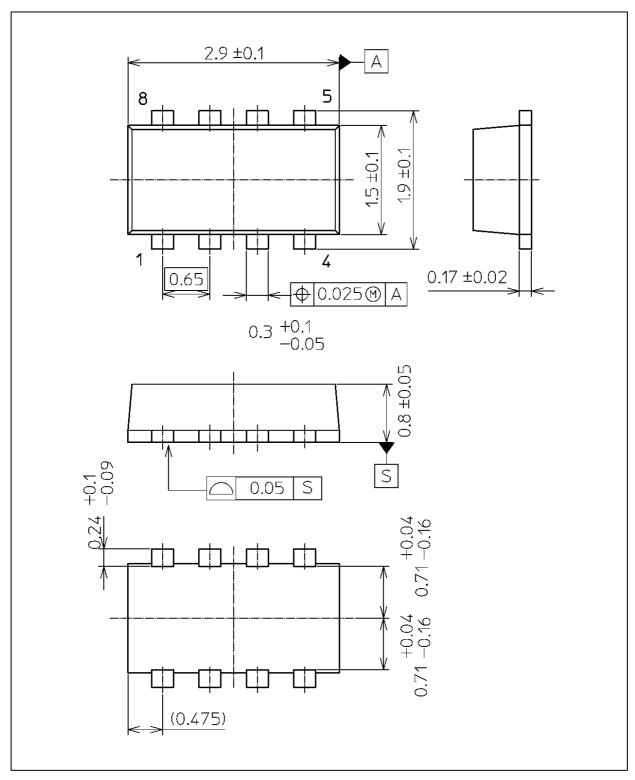
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

TPCF8004

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)

TOSHIBA: 2-3U1S

Nickname: VS-8

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